

isc Silicon PNP Power Transistor

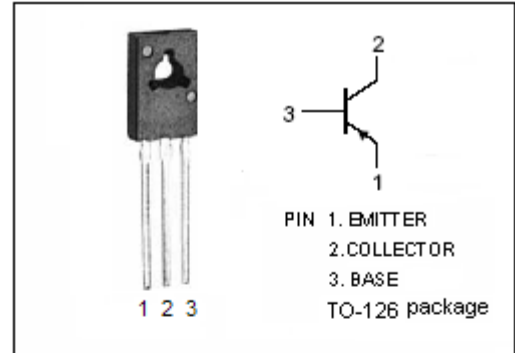
2N5415

DESCRIPTION

- PNP high-voltage transistor
- Low current (max. 200 mA)
- High voltage (max. 300 V)

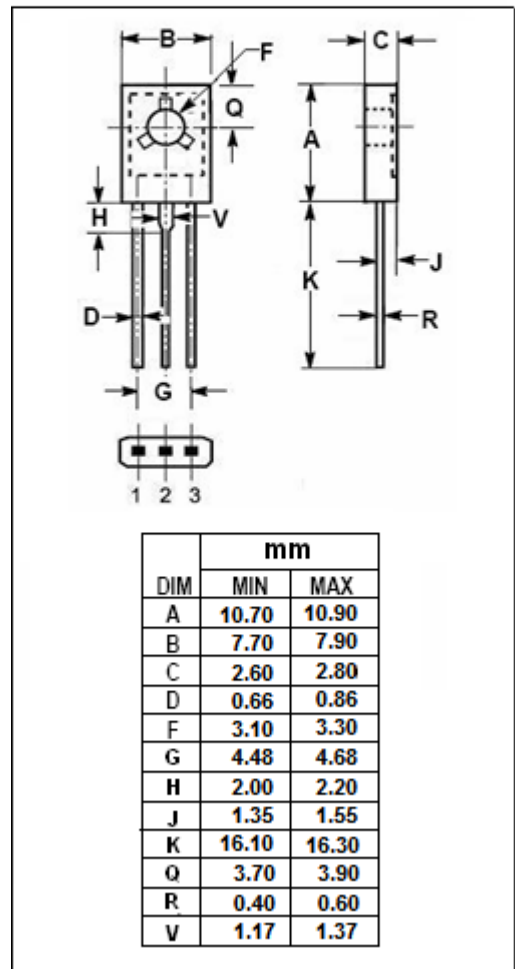
APPLICATIONS

- Designed for Switching and linear amplification in military, industrial and consumer equipment applications.



ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Base Voltage	200	V
V _{CEO}	Collector-Emitter Voltage	200	V
V _{EBO}	Emitter-Base Voltage	4	V
I _C	Collector Current-Continuous	0.2	A
I _{CM}	Peak Collector Current	0.4	A
I _{BM}	Peak Base cCurrent	0.2	A
P _C	Collector Power Dissipation @ T _a <50°C	1.0	W
	Collector Power Dissipation @ T _C =25°C	10	
T _J	Junction Temperature	200	°C
T _{stg}	Storage Temperature Range	-60~200	°C



isc Silicon PNP Power Transistor**2N5415****ELECTRICAL CHARACTERISTICS** $T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C= 50\text{mA}; I_B= 5\text{mA}$			0.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB}= 175\text{V}; I_E= 0$			50	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB}= 4\text{V}; I_C= 0$			20	μA
h_{FE}	DC Current Gain	$I_C= 50\text{mA}; V_{CE}= 10\text{V}$	30		150	
f_T	Current-Gain—Bandwidth Product	$I_C= 10\text{mA}; V_{CE}= 10\text{V}$	15			MHz